

BD376/378/380

Medium Power Linear and Switching Applications

Complement to BD375, BD377 and BD379 respectively



PNP Epitaxial Silicon Transistor

1. Emitter 2.Collector 3.Base

Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage : BD376	- 50	V
	: BD378	- 75	V
	: BD380	- 100	V
V _{CEO}	Collector-Emitter Voltage : BD376	- 45	V
	: BD378	- 60	V
	: BD380	- 80	V
V _{EBO}	Emitter-Base Voltage	- 5	V
I _C	Collector Current (DC)	- 2	А
I _{CP}	*Collector Current (Pulse)	- 3	Α
I _B	Base Current	- 1	Α
P _C	Collector Dissipation (T _C =25°C)	25	W
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

Electrical Characteristics $T_C=25$ °C unless otherwise noted

Symbol	Parame	ter	Test Condition	Min.	Тур.	Max.	Units
V _{CEO} (sus)	*Collector-Emitter Sustain	ing Voltage					
		: BD376	$I_C = -100 \text{mA}, I_B = 0$	- 45			V
		: BD378		- 60			V
		: BD380		- 80			V
BV _{CBO}	Collector-Base	: BD376	$I_C = -100 \mu A, I_E = 0$	- 50			V
	Breakdown Voltage	: BD378		- 75			V
		: BD380		- 100			V
I _{CBO}	Collector Cut-off Current	: BD376	$V_{CB} = -45V, I_{E} = 0$			- 2	μΑ
		: BD378	$V_{CB} = -60V, I_{E} = 0$			- 2	μΑ
		: BD380	$V_{CB} = -80V, I_{E} = 0$			- 2	μΑ
I _{EBO}	Emitter Cut-off Current		$V_{EB} = -5V, I_{C} = 0$			- 100	μΑ
h _{FE1}	*DC Current Gain		$V_{CE} = -2V, I_{C} = -0.15A$	40		375	
h _{FE2}			$V_{CE} = -2V, I_{C} = -1A$	20			
V _{CE} (sat)	*Collector-Emitter Saturati	on Voltage	$I_C = -1A, I_B = -0.1A$			- 1	V
V _{BE} (on)	*Base-Emitter ON Voltage	!	$V_{CE} = -2V, I_{C} = -1A$			- 1.5	V
t _{ON}	Turn ON Time		$V_{CC} = -30V, I_{C} = -0.5A$		50		ns
t _{OFF}	Turn OFF Time		$I_{B1} = -I_{B2} = -0.05A$ $R_{L} = 60\Omega$		500		ns

^{*} Pulse Test: PW=350μs, duty Cycle=2% Pulsed

h_{FE} Classificntion

Classification	6	10	16	25
h _{FE1}	40 ~ 100	63 ~ 160	100 ~ 250	150 ~ 375

Typical Characteristics



Figure 1. DC current Gain

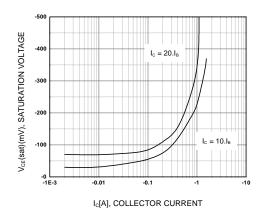


Figure 2. Collector-Emitter Saturation Voltage

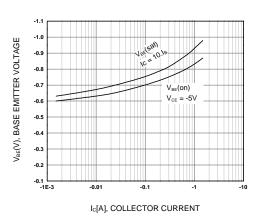


Figure 3. Base-Emitter Voltage

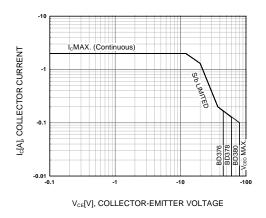


Figure 4. Safe Operating Area

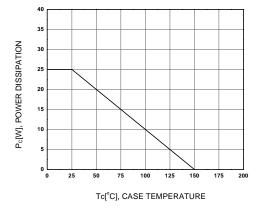
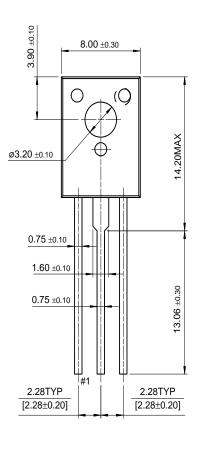


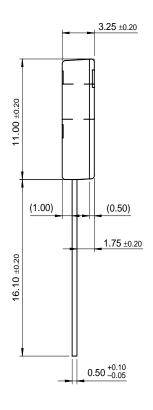
Figure 5. Power Derating

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Package Demensions



Dimensions in Millimeters

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